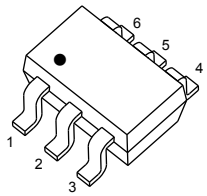
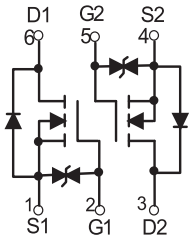
SOT-363 Plastic-Encapsulate MOSFETS

$V_{(BR)DSS}$	$R_{DS(on)}$MAX	I_D
60 V	2.5Ω@10V	340mA
	3Ω@4.5V	

SOT-363



Equivalent Circuit



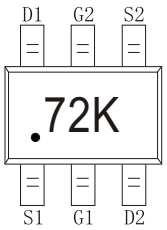
FEATURE

- High density cell design for Low $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability
- ESD protected

APPLICATION

- Load Switch for Portable Devices
- DC/DC Converter

MARKING



MOSFET MAXIMUM RATINGS (T_a = 25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{DS}	Drain-Source voltage	60	V
V_{GS}	Gate-Source voltage	±20	V
I_D	Drain Current	340	mA
P_D	Power Dissipation	0.15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃
$R_{\theta JA}$	Thermal Resistance fromJunction to Ambient	833	℃ /W

MOSFET ELECTRICAL CHARACTERISTICS

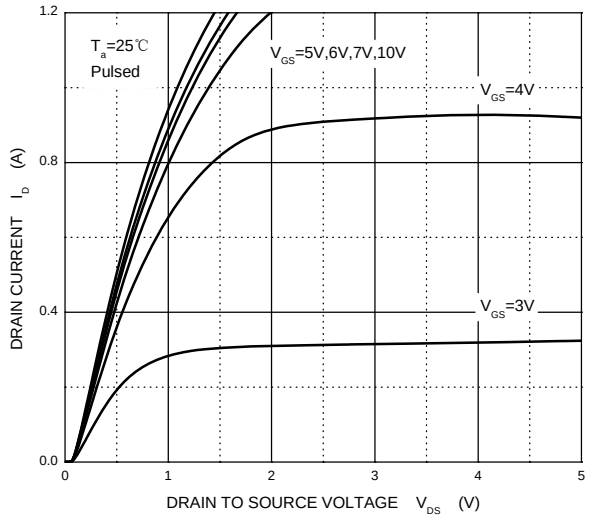
T_a=25℃ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Characteristics						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0V, I_D =250μA	60			V
Gate Threshold Voltage*	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =1mA	1	1.3	2.5	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =48V,V_{GS} = 0V			1	μA
Gate –Source leakage current	I_{GSS1}	V_{GS} =±20V, V_{DS} = 0V			±10	μA
Drain-Source On-Resistance*	$R_{DS(on)}$	V_{GS} = 4.5V, I_D =200mA		1.1	3	Ω
		V_{GS} =10V,I_D =500mA		0.9	2.5	Ω
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=300mA			1.5	V
Recovered charge	Q_r	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		nC
Dynamic Characteristics**						
Input Capacitance	C_{iss}	V_{DS} =10V,V_{GS} =0V,f =1MHz			40	pF
Output Capacitance	C_{oss}				30	pF
Reverse Transfer Capacitance	C_{rss}				10	pF
Switching Characteristics**						
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V,V_{DD}=50V,R_G=50Ω, R_{GS}=50Ω, R_L=250Ω			10	ns
Turn-Off Delay Time	$t_{d(off)}$				15	ns
Reverse recovery Time	t_{rr}	V_{GS}=0V,I_S=300mA,V_R=25V, dI_S/dt=-100A/μs		30		ns
GATE-SOURCE ZENER DIODE						
Gate-Source Breakdown Voltage	BV_{GSO}	I_{gs}=±1mA (Open Drain)	±21.5		±30	V

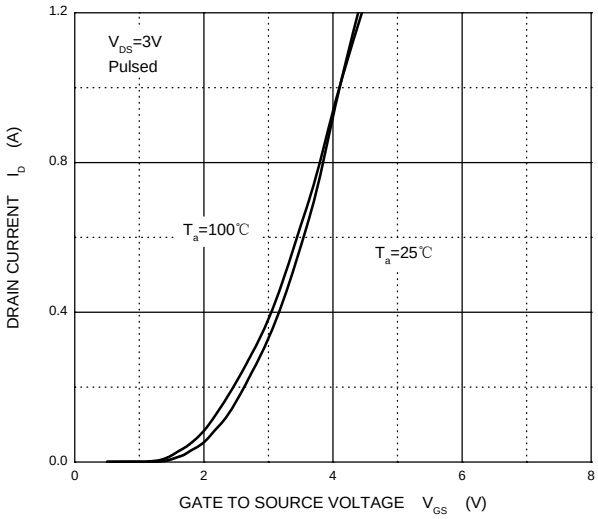
Notes :
*Pulse Test : Pulse Width ≤300μs, Duty Cycle ≤2%.
**These parameters have no way to verify.

Typical Characteristics

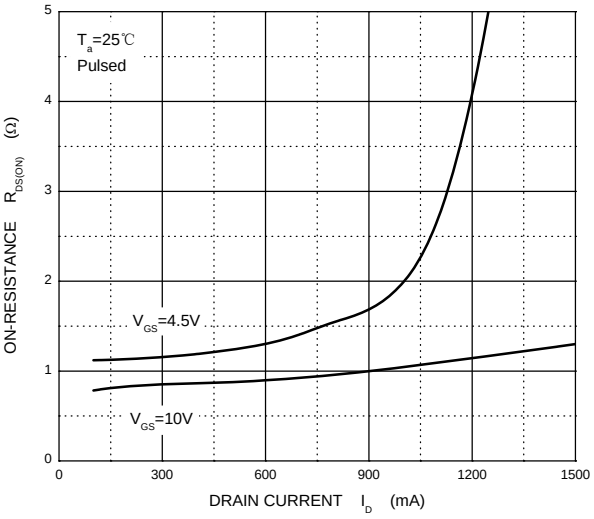
Output Characteristics



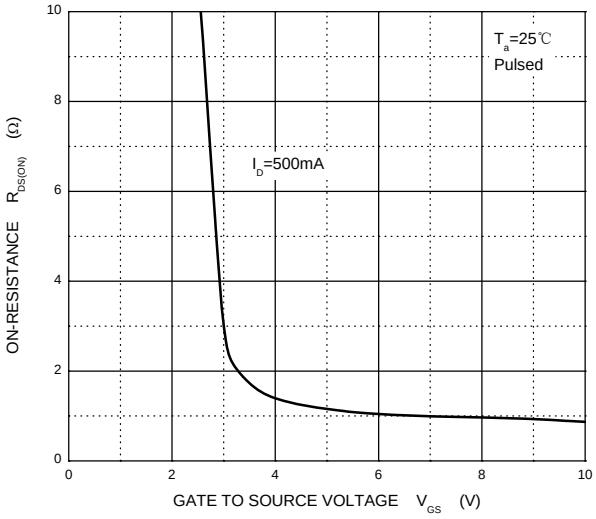
Transfer Characteristics



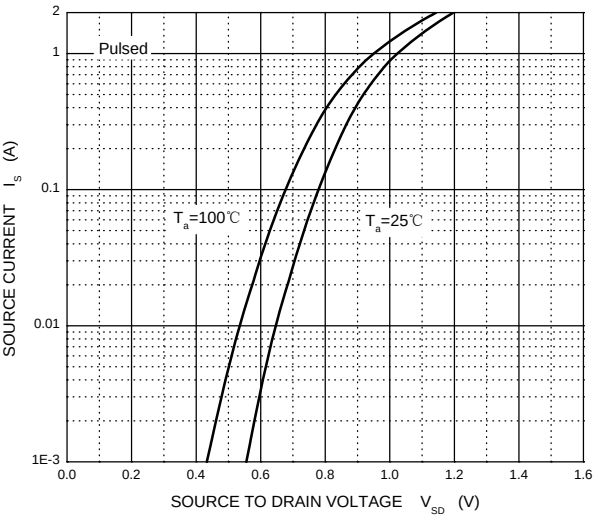
$R_{DS(ON)}$ —— I_D



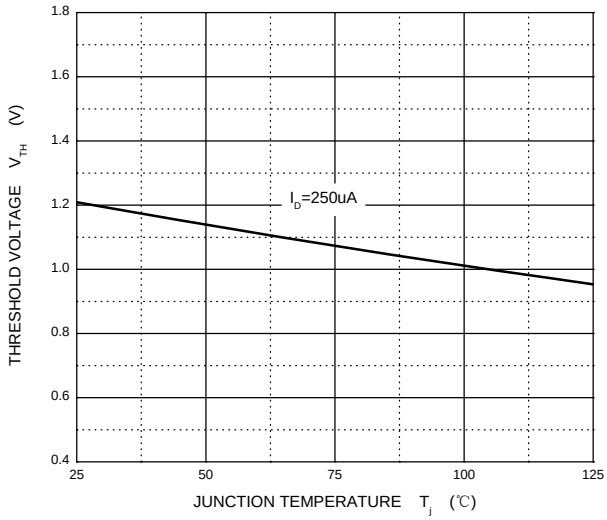
$R_{DS(ON)}$ —— V_{GS}

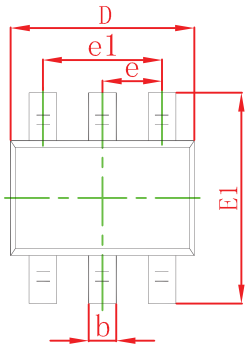


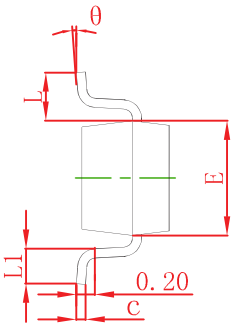
I_S —— V_{SD}

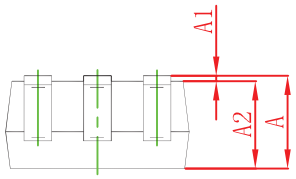


Threshold Voltage



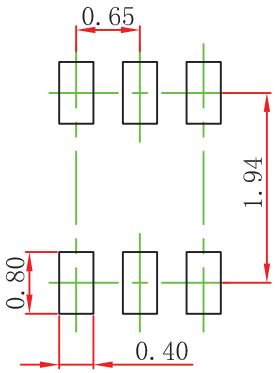






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-363 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.